Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK1061

High Speed Switching Applications
Analog Switch Applications
Interface Applications

- Excellent switching times: ton = 14 ns (typ.)
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ mS (min)}$
- Low on resistance: RDS (ON) = 0.6Ω (typ.)
- Enhancement-mode
- Complementary to 2SJ167

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC	ΙD	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation (Ta = 25°C)		P _D	300	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

0.55MAX.

0.4

1.27

1.27

1.27

1.27

2.3

SOURCE

2. DRAIN

3. GATE

JEDEC

JEITA

TOSHIBA

2-4E1E

Weight: 0.13 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

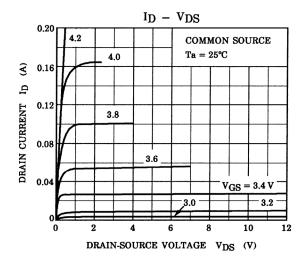


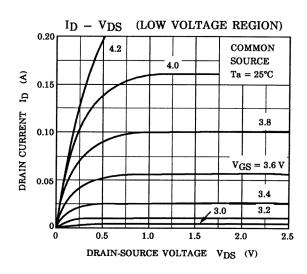
Electrical Characteristics (Ta = 25°C)

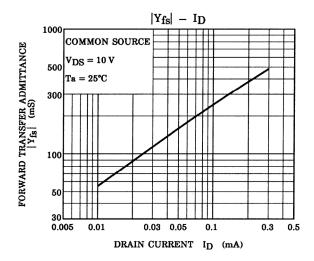
Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±100	nA
Drain cut-off current		I _{DSS}	V _{DS} = 60 V, V _{GS} = 0	_	_	10	μΑ
Drain-source breakdown voltage		V (BR) DSS	I _D = 1 mA, V _{GS} = 0	60	_	_	V
Gate threshold voltage		V _{th}	V _{DS} = 10 V, I _D = 1 mA	2	_	3.5	V
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 50 mA	100	_	_	mS
Drain-source ON	resistance	R _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		0.6	1.0	Ω
Drain-source ON	voltage	V _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		30	50	mV
Input capacitance		C _{iss}			55	65	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		13	18	pF
Output capacitance		Coss			40	50	pF
Switching time	Rise time	t _r	10 V V _{IN} I _D = 100 mA V _{OUT} V _{IN} V _{DD} = 30 V	_	8	_	
	Turn-on time	t _{on}			14	_	- ns
	Fall time	t _f		_	35	_	
	Turn-off Time	t _{off}	$D.U. \le 1\%$ $V_{IN}: t_r, t_f < 5 \text{ ns}$ $(Z_{Out} = 50 \Omega)$	_	75	_	

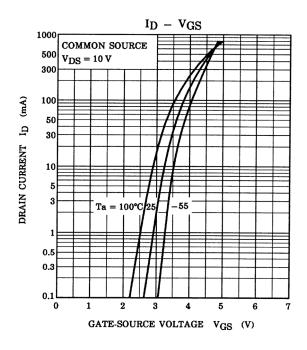
Note: This transistor is the electrostatic sensitive device. Please handle with caution.

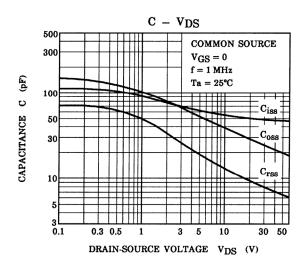
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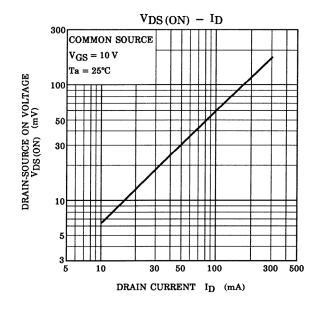


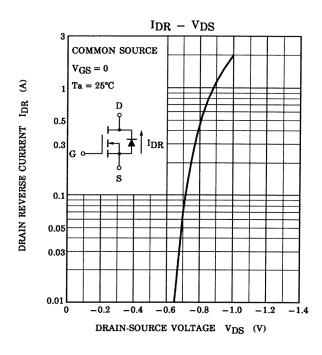


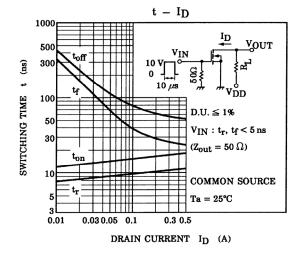


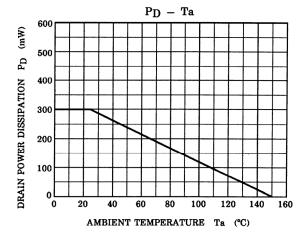


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20070701-EN GENERAL

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